

L1200-35K00

 stem type LED with epoxy resin lens

L1200-35K00 is an InGaAsP LED mounted on a TO-46 stem with a spherical glass lens being designed for high output power uses.

On forward bias, it emits a spectral band of radiation, which peaks at 1200nm.

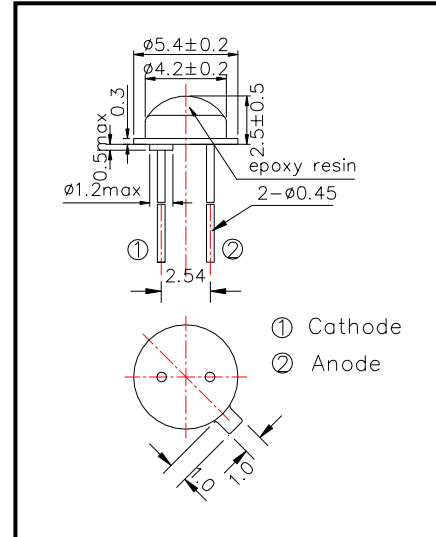
◆ Features

- 1) Wide viewing angle
- 2) High Reliability

◆ Specifications

- | | |
|---------------------|------------------------|
| 1) Product Name | Near Infrared LED Lamp |
| 2) Type No. | L1200-35K00 |
| 3) Chip Spec. | |
| (1) Material | InGaAsP |
| (2) Peak Wavelength | 1200nm |
| 4) Package | |
| (1) Type | TO-46 stem |
| (2) Lens | Epoxy resin lens |
| (3) Cap | Gold plated |

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P_D	120	mW	$T_a=25^\circ\text{C}$
Forward Current	I_F	100	mA	$T_a=25^\circ\text{C}$
Pulse Forward Current	I_{FP}	1000	mA	$T_a=25^\circ\text{C}$
Reverse Voltage	V_R	5	V	$T_a=25^\circ\text{C}$
Operating Temperature	T_{OPR}	-30 ~ +90	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-30 ~ +100	$^\circ\text{C}$	
Soldering Temperature	T_{SOL}	260	$^\circ\text{C}$	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

◆ Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V_F	$I_F=50\text{mA}$		1.10	1.40	V
Reverse Current	I_R	$V_R=5\text{V}$			10	μA
Total Radiated Power	P_O	$I_F=50\text{mA}$		3.5		mW
Peak Wavelength	λ_P	$I_F=50\text{mA}$	1150	1200	1250	nm
Half Width	$\Delta\lambda$	$I_F=50\text{mA}$		100		nm
Viewing Half Angle	$\theta_{1/2}$	$I_F=50\text{mA}$		± 50		deg.
Rise Time	t_r	$I_F=50\text{mA}$		10		ns
Fall Time	t_f	$I_F=50\text{mA}$		10		ns

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.